



# KISAB

## PRODUCT SPECIFICATIONS

## Product specifications

<b>Silicon carbide substrate material specification</b>	
<b>Property</b>	<b>Value</b>
Polytype	4H polytype
Orientation	4.0
Diameter	150 mm
Center thickness	350 $\mu\text{m}$
Bow	<5 $\mu\text{m}$
Warp	<15 $\mu\text{m}$
TTV	<4 $\mu\text{m}$
Surface treatment (Si-face)	Epi-ready
Resistivity	19-21 m $\Omega\text{cm}$
Resistivity uniformity	<2%

<b>Defect density</b>	
<b>Property</b>	<b>Value</b>
Micropipes (MP)	None
Basal plane dislocation density (BPD)	79% of area none 90 % of area < 20 $\text{cm}^{-2}$
Threading screw dislocation density (TSD)	Very low
Threading edge dislocation density (TED)	28% < 1200 $\text{cm}^{-2}$ 58% < 2000 $\text{cm}^{-2}$ 83% < 3200 $\text{cm}^{-2}$ 90 % < 4000 $\text{cm}^{-2}$ 97 % < 6000 $\text{cm}^{-2}$
<b>Packaging</b>	
Cassettes or single wafers	